

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL JUNCTION TYPE

2SJ104

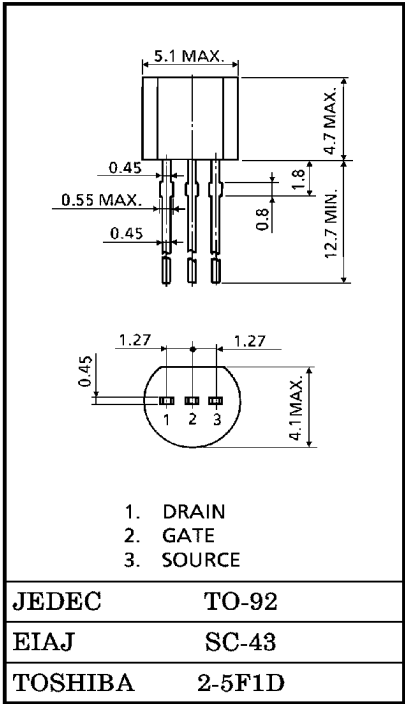
FOR AUDIO AMPLIFIER, ANALOG SWITCH, CONSTANT CURRENT AND IMPEDANCE CONVERTER APPLICATIONS

Unit in mm

- High Input Impedance : $I_{GSS}=1.0nA$ (Max.) ($V_{GS}=25V$)
- Low $R_{DS(ON)}=40\Omega$ (Typ.) ($I_{DSS}=-5mA$)
- Complimentary to 2SK364

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDS}	25	V
Gate Current	I_G	-10	mA
Drain Power Dissipation	P_D	400	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55~125	°C



Weight : 0.21g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	I_{GSS}	$V_{GS}=25V, V_{DS}=0$	—	—	1.0	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDS}$	$V_{DS}=0, I_G=100\mu A$	25	—	—	V
Drain Current	I_{DSS} (Note 1)	$V_{DS}=-10V, V_{GS}=0$	-2.6	—	-20	mA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS}=-10V, I_D=-0.1\mu A$	0.2	—	2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=-10V, V_{GS}=0,$ $f=1kHz$ (Note 2)	12	30	—	mS
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0, f=1MHz$	—	105	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DG}=-10V, I_D=0, f=1MHz$	—	32	—	pF
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{DS}=-10mV, V_{GS}=0$ (Note 2)	—	40	—	Ω

Note 1 : I_{DSS} Classification GR : -2.6~-6.5mA, BL : -6~-12mA, V : -10~-20mA

Note 2 : Condition of the typical value $I_{DSS}=-5mA$

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